

PREPARATION AND FAR INFRARED PROPERTIES OF CdIn₂Te₄

AND ZnIn₂Te₄

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ABSTRACT: Semiconducting polycrystals of the compound, CdIn₂Te₄ and ZnIn₂Te₄, were obtained using the Bridgeman procedure. Crystallographic properties were measured and also far infrared reflectivity was measured in the range between 40 and 400 cm⁻¹. The experimental data were numerically analysed and ionic bonds in both compounds discussed. The influence on the ionic bonds of the replacement of Cd atoms with Zn was also analysed.

1. INTRODUCTION

Many papers about A^{II}₂B^{III}₂C^{VI}₄ compounds have recently been published. However, attention has mostly been paid to HgIn₂Te₄ /1/, then ZnIn₂S₄ /2,3,4/ and partly to cadmium gallium chalcogenides for instance CdGa₂S₄, CdGa₂Se₄ and CdGa₂Te₄ /5,6,7/. All of them have the S₄² structure. The properties of these compounds can be studied by observing the properties of the two component compounds. Thus, for CdIn₂S₄ they are CdS and In₂S₃ /6/.

As far as we know there are only two published papers concerning CdIn₂Te₄, one about its crystallographic characteristics /8/ and the other recording some optical properties in the visible range /9/.

The compound ZnIn₂Te₄ has not been studied yet. Except that its crystallographic properties were observed by Hahn /8/ a long time ago.

Generally, A^{II}₂B^{III}₂C^{VI}₄ compounds are studied because of their well exposed photoconductive properties.

In this work the way of preparation, crystallographic and far infrared optical properties of CdIn_2Te_4 and ZnIn_2Te_4 were investigated.

2. Experimental

Polycrystalline samples of CdIn_2Te_4 and ZnIn_2Te_4 were obtained using the Bridgeman procedure. The elements of at least 99.9990% purity and in stoichiometric proportion were placed in a quartz tube which was evacuated to about 10^{-5} mmHg and then sealed off. The ampoules were put in a vertical furnace which was heated to about 1050°C . After several hours the ampoule was lowered down into the cooler zone at a speed of about 1mm/h. It was confirmed that the produced crystals were single faced polycrystals by x-ray powder photography. The calculated values of lattice parameters were $a=6.11 \text{ \AA}$ and $c = 12.22 \text{ \AA}$ for ZnIn_2Te_4 and $a=6.205 \text{ \AA}$ and $c=12.405 \text{ \AA}$ for CdIn_2Te_4 .

The specimens for optical measurements were cut from ingots. Slices were between 0.5 and 1mm thick. The samples were then polished on one side using a conventional polishing technique.

The far infrared reflectivity measurements were performed using a Beckmann FS 720 Fourier spectrometer. The variation of near normal incident reflectivity for CdIn_2Te_4 and ZnIn_2Te_4 are given in figures 1 a and 1 b respectively, where the experimental data are represented by squares. The solid lines were calculated using the oscillator parameters, which were obtained by numerical analysis carried out with the aid of a fitting procedure,

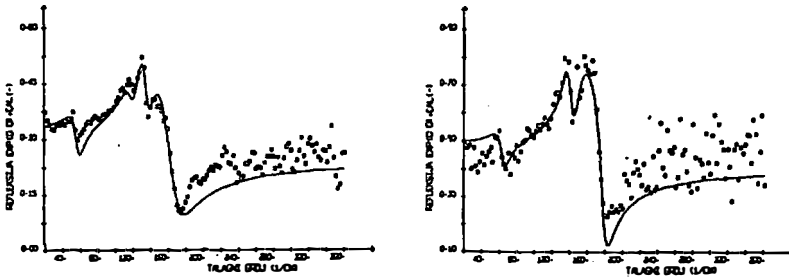


Fig. 1. Far infrared reflectivity of CdIn_2Te_4 (a) and ZnIn_2Te_4 (b). The solid lines were calculated using the oscillator parameters given in Table 1 .

according to the Gervais four parameters model. /10/. The values of transversal (ω_{TO}) and longitudinal (ω_{LO}) optical modes and their damping factors (γ_{TO} and γ_{LO}) for four oscillators of $CdIn_2Te_4$ and three oscillators of $ZnIn_2Te_4$ are given in Table 1. Table 1.

	$CdIn_2Te_4$				$ZnIn_2Te_4$		
	I	II	III	IV	I	II	III
$\omega_{TO} (cm^{-1})$	75.5	138	151	163.5	82	155	171
$\omega_{LO} (cm^{-1})$	78	140	156.5	189	85	163	200
$\gamma_{TO} (cm^{-1})$	13.5	13	12	22.5	14	8	11
$\gamma_{LO} (cm^{-1})$	9.5	10	9.5	23.5	9.5	7	9
ϵ_{∞}	8.5				20		

The real $Re(\epsilon(\omega))$ (—) and imaginary $Im(\epsilon(\omega))$ (---) parts of the complex dielectric function for both compounds are given in figures 2a and 2b.

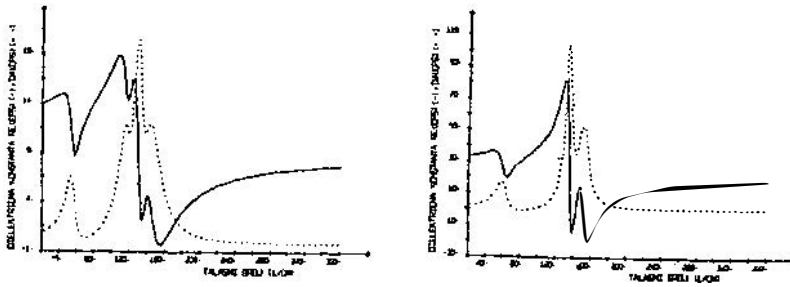


Fig. 2. Real and imaginary parts of the complex dielectric function of $CdIn_2Te_4$ (a) and $ZnIn_2Te_4$ (b)

3. DISCUSSION

The number of infrared and Raman active modes were calculated for $CdIn_2Te_4$ and $ZnIn_2Te_4$ using Adams-Newton Tables /11/. Since their tetragonal lattice structure, space group S_4^2 and Wyckoff's sites were known, the complete number of these modes was:

$$\Gamma = 3A+6B+6E .$$

The number of acoustical modes is $N_A=3$ and they have the symmetry (B+E). In that case there are three (3A) Raman active

modes and 10 infrared active modes. (5B+5E), five for $E_{\perp c}$ and five for $E//c$.

In this work we have observed only four and three infrared active modes for $CdIn_2Te_4$ and $ZnIn_2Te_4$, respectively. That means that the nonobserved oscillators should be much weaker compared with the observed ones. They probably were not observed for two reasons. First, the level of noisy was of a similar height to the signal and secondly the crystals were polycrystalline so that oscillators for $E//c$ and $E_{\perp c}$ could overlap. It is very interesting to compare the oscillators with the highest wavenumber for both compounds. Judging by Fig. 1a and 1b it is about 163 cm^{-1} for $CdIn_2Te_4$ and about 170 cm^{-1} for $ZnIn_2Te_4$. This is as expected because Cd has a larger atomic weight than Zn. If we make a similar comparison between $CdIn_2Te_4$ and $CdGa_2Te_4$ we can see that the position of the observed oscillator is moved much further to about $210\text{ cm}^{-1} / 12$. When the heavier atoms of In are replaced with the much lighter Ga.

From these data one can conclude that the roles of the ionic bond between Cd and In atoms is relatively more important than that of the ionic bonds between these and the chalcogenide elements.

4. References

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